

Description

The SX90N06T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 60V$ $I_D = 90A$

$R_{DS(ON)} < 7.0m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)**

Symbol	Parameter	Value	Unit
V_{DS}	Drain source voltage	60	V
V_{GS}	Gate source voltage	± 20	V
I_D	Continuous drain current ¹⁾	90	A
I_{DM}	Pulsed drain current ²⁾	320	A
I_S	Diode forward current	37	A
I_{SP}	Pulsed source current	210	A
P_D	Power dissipation	108	W
EAS	Single pulsed avalanche energy ³⁾	205.4	mJ
T_{stg}, T_j	Operation and storage temperature	-55 to 150	°C
$R_{\theta JC}$	Thermal resistance, junction-case	1.4	°C/W
$R_{\theta JA}$	Thermal resistance, junction-ambient ⁴⁾	62.5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	60	64	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}, V_{GS}=0\text{V},$	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.0	3.0	4.0	V
RDS(on)	Static Drain-Source on-Resistance note	$V_{GS}=10\text{V}, I_D=30\text{A}$	-	5.8	7.0	$\text{m}\Omega$
C_{iss}	Input Capacitance	$V_{DS}=30\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$	-	4136	-	pF
C_{oss}	Output Capacitance		-	286	-	pF
C_{rss}	Reverse Transfer Capacitance		-	257	-	pF
Q_g	Total Gate Charge	$V_{DS}=30\text{V}, I_D=30\text{A}, V_{GS}=10\text{V}$	-	90	-	nC
Q_{gs}	Gate-Source Charge		-	9	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	18	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30\text{V}, I_D=30\text{A}, R_G=1.8\Omega, V_{GS}=10\text{V}$	-	9	-	ns
t_r	Turn-on Rise Time		-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	40	-	ns
t_f	Turn-off Fall Time		-	15	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	90	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	320	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=30\text{A}$	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	$I_F=30\text{A}, dI/dt=100\text{A}/\mu\text{s}$	-	33	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	46	-	nC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width . The EAS data shows Max. rating .
- 3、The test cond $\leq 300\mu\text{s}$ duty cycle $\leq 2\%$, duty cycle ition is $T_J =25^\circ\text{C}$, $VDD =35\text{V}$, $VG =10\text{V}$, $R G =25\Omega$, $L=0.5\text{mH}$, $I_{AS} =21\text{A}$
- 4、The power dissipation is limited by 175°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Electrical Characteristics Diagrams

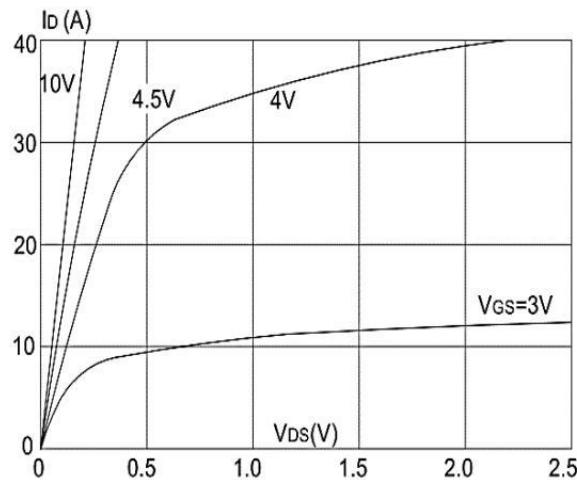


Figure 1: Output Characteristics

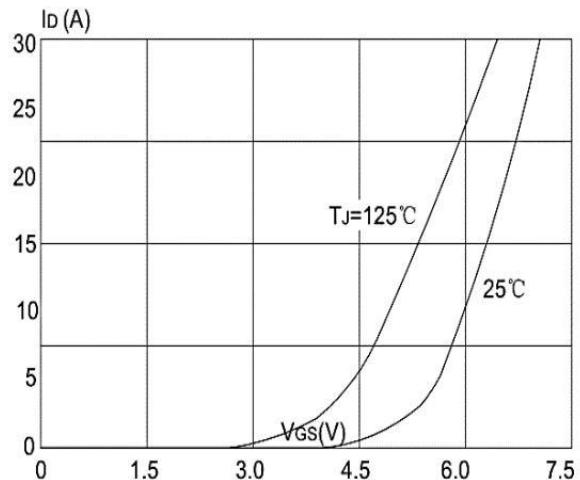


Figure 2: Typical Transfer Characteristics

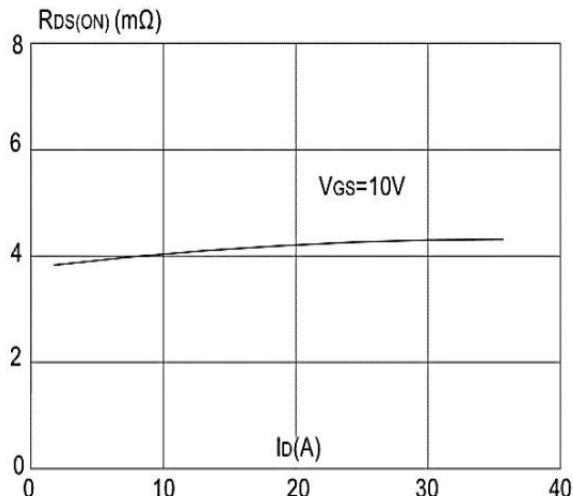


Figure 3: On-resistance vs. Drain Current

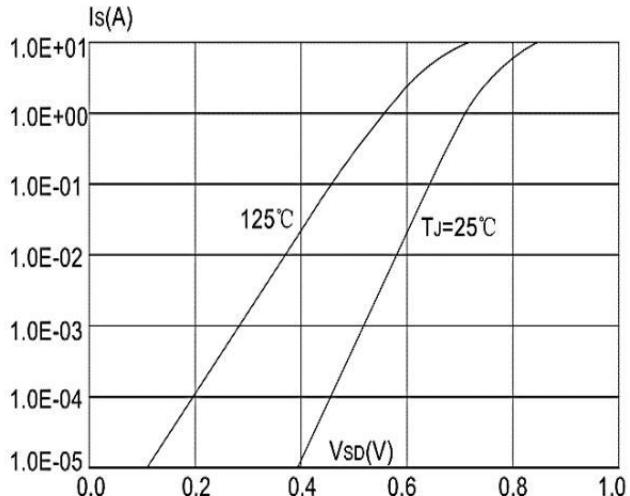


Figure 4: Body Diode Characteristics

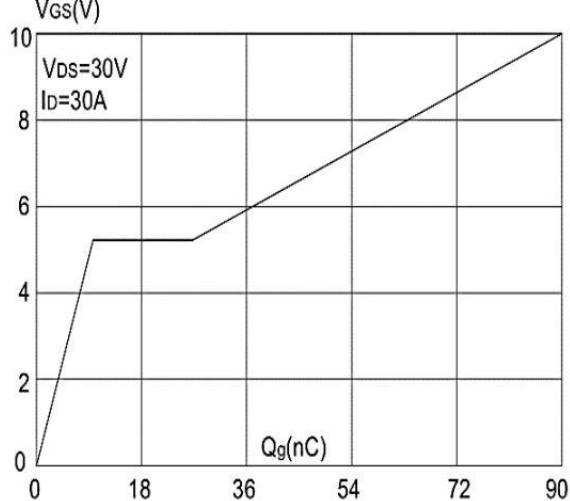


Figure 5: Gate Charge Characteristics

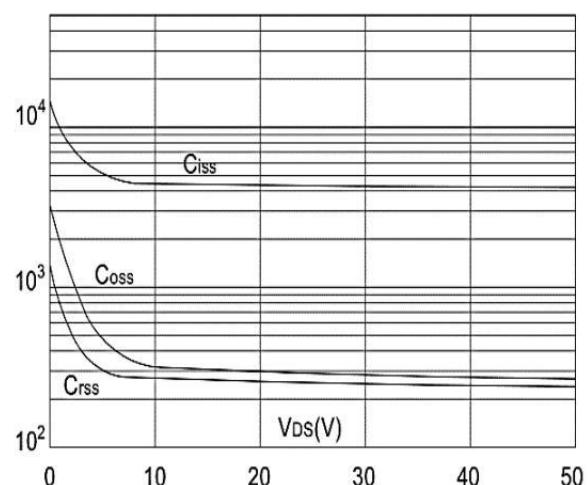


Figure 6: Capacitance Characteristics

Typical Characteristics

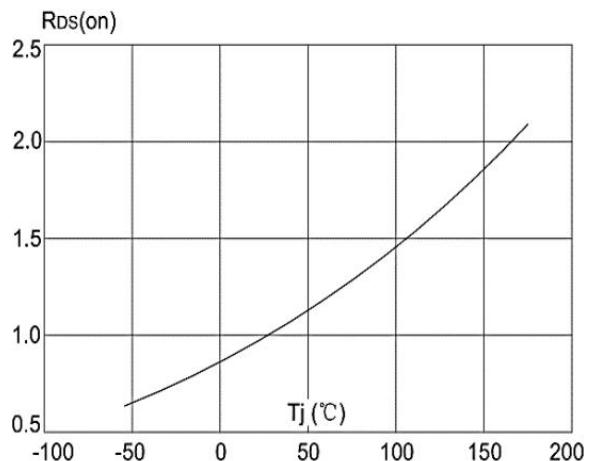
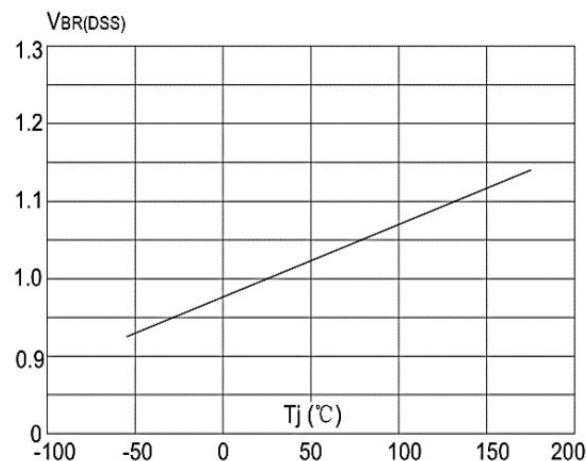


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

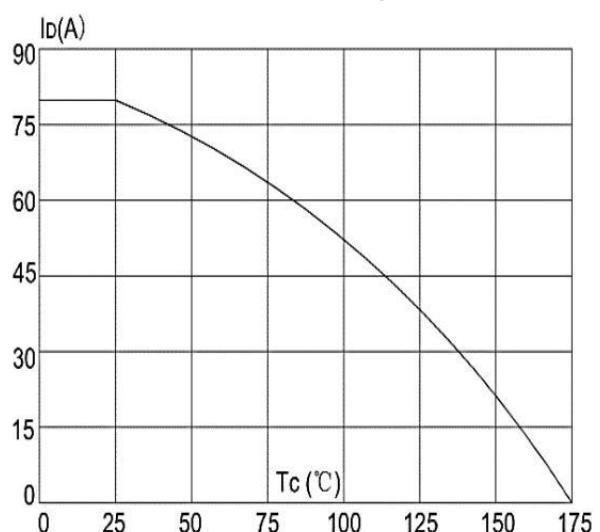
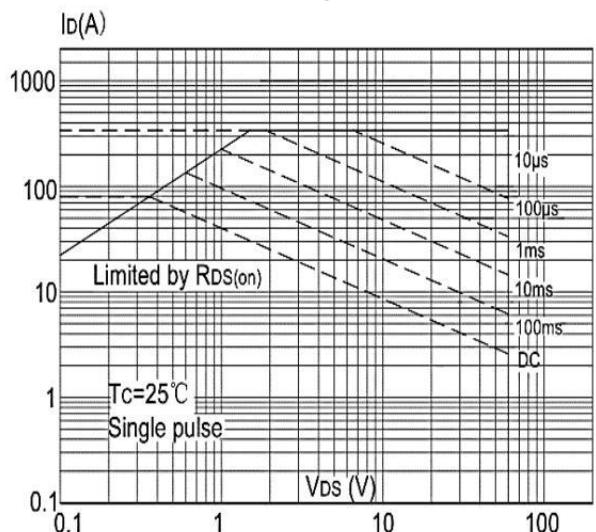


Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

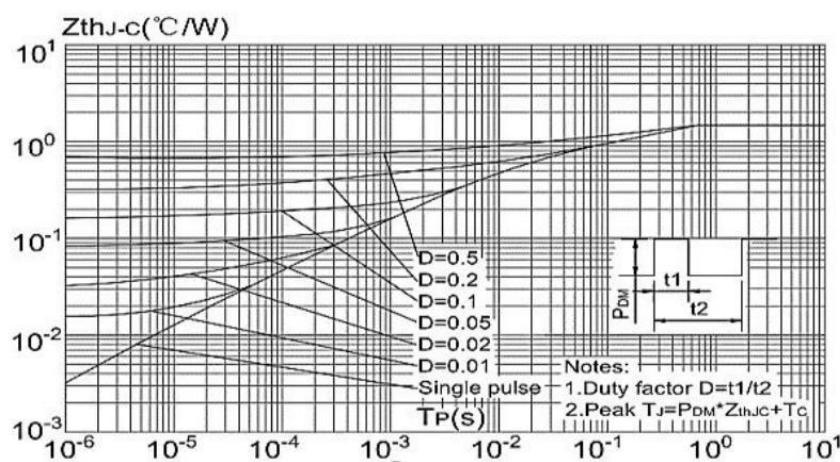
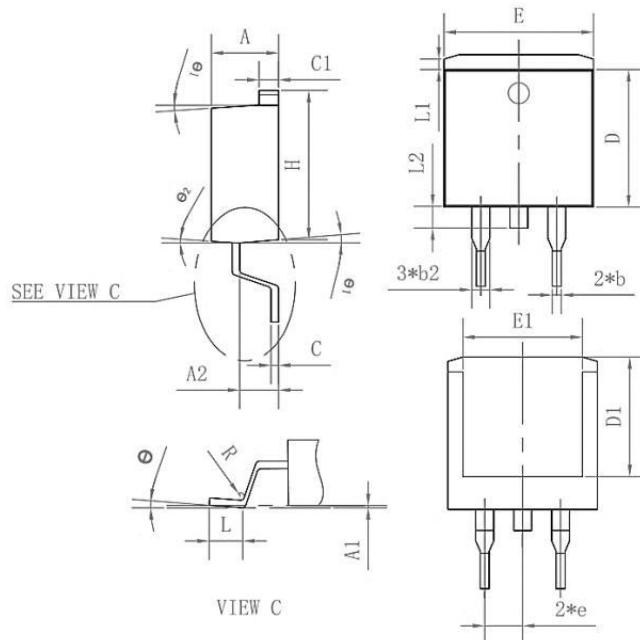


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Package Mechanical Data-TO-263-3L-SLK



Symbol	Common		
	mm		
	Mim	Nom	Max
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.70
b	0.70	0.80	1.00
b2	1.25	1.36	1.50
C	0.45	0.50	0.65
C1	1.29	1.30	9.40
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70
e	-	2.54	-
L	2.34	2.54	2.74
L1	1.00	1.10	1.20
L2	1.30	1.40	1.50
R	0.24	0.25	0.26
θ	0°	4°	8°
Θ1	4°	7°	10°
Θ2	0°	3°	6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-263-3L		800